

**THE CLAIMS:**

Please amend the claims as follows. This listing of the claims is the current listing of claims after entry of the amendments.

1-20. (Cancelled).

21. (Previously Presented) A process for photo-fabricating a three-dimensional object by selectively curing a photo-curable resin composition comprising:

- (a) an oxetane having two or more oxetane rings;
- (b) an epoxy compound; and
- (c) a cationic photoinitiator,

wherein said process comprises

- (i) forming a layer of said composition;
- (ii) selectively irradiating said layer of said composition to form a solid cured resin layer;
- (iii) forming a layer of said composition on the solid cured resin layer; and
- (iv) repeating steps (ii) and (iii).

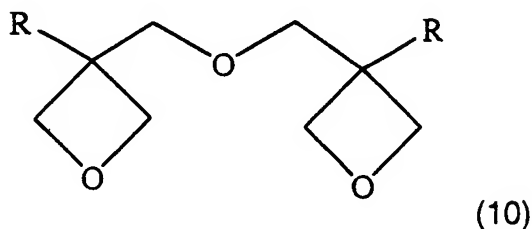
22. (Previously Presented) A process for photo-fabricating a three-dimensional object by selectively curing a photo-curable resin composition comprising:

- (a) an oxetane;
- (b) an epoxy compound; and
- (c) a cationic photoinitiator,

wherein said process comprises

- (i) forming a layer of said composition;
- (ii) selectively irradiating said layer of said composition to form a solid cured resin layer;
- (iii) forming a layer of said composition on the solid cured resin layer; and
- (iv) repeating steps (ii) and (iii);

wherein said oxetane is represented by the following formula (10):



wherein R represents a hydrogen atom; a fluorine atom; an alkyl group having from 1 to 6 carbon atoms; a fluoroalkyl group having from 1 to 6 carbon atoms; an aryl group having from 6 to 18 carbon atoms; a furyl group; or a thienyl group.

23. (Previously Presented) The process of claim 22, wherein each R represents an alkyl group having from 1 to 6 carbon atoms.

24. (Previously Presented) The process of claim 22, wherein each R represents an ethyl group.

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- a source electrode 35, 37 overlapping the gate electrode 29 and the first semiconductor layer 33 and contacting another one of the two parts of the second semiconductor layer 39; and
- a drain electrode 43, 45 overlapping the gate electrode 29 and the first semiconductor layer 33 and contacting another one of the two parts of the second semiconductor layer 39;
- wherein the source 35, 37 and the drain electrode 43, 45 define a channel region in the first semiconductor layer 33 having a length between the first and second portions of the first semiconductor layer and a width the same as the width of at least one of the two parts of the second semiconductor layer such that the ratio of the width to the length (W/L) of the channel region is in a range of 8 to 10.

The thin film transistor disclosed in document (1) therefore discloses all the features of that now claimed. The subject matter of claim 1 is therefore not new; claim 1 is not allowable.

The equivalent claim 9 merely comprises general steps for fabricating a thin film transistor. Even without explicitly defining the process, the thin film transistor disclosed in document (1) is fabricated using the process steps of claim 9. Thus, the process claimed in claim 9 is anticipated by document (1) so as to damage its novelty. Claim 9 is therefore not allowable.

III

70. (New) The process of claim 68, wherein an H-shaped object obtained by curing said composition has a dimensional accuracy value of less than or equal to 0.10 mm.

71. (New) A three-dimensional object obtained by the process of claim 68.

72. (New) A three-dimensional object obtained by the process of claim 69.

73. (New) A three-dimensional object obtained by the process of claim 70.

74. (New) A radiation-curable composition comprising:

(a) an epoxidated compound obtained by a process comprising epoxidating a double bond between carbons of a corresponding compound having an ethylenically unsaturated bond using an appropriate oxidizing agent such as hydrogen peroxide or peroxy acid process;

(b) a polyfunctional monomer;

(c) a polyhydric alcohol;

(d) an oxetane compound having one or more oxetanes groups;

(e) one or more free-radical photoinitiators; and

(f) one or more cationic photoinitiators.

75. (New) The radiation-curable composition according to claim 74, wherein said composition further comprises a pigment and/or a dye.

76. (New) The radiation-curable composition according to claim 75, wherein said composition further comprises one or more additives different than the pigment or dye.

77. (New) A radiation-curable composition used in photo-fabrication of object comprising:

(a) an epoxidated compound obtained by a process comprising epoxidating a double bond between carbons of a corresponding compound having an ethylenically unsaturated bond using an appropriate oxidizing agent such as hydrogen peroxide or peroxy acid process;

(b) pentaerythritol tetra (meth)acrylate;

(c) propoxylated modified glycerol;

(d) 3-ethyl-3-hydroxymethyloxetane;

(e) a free-radical photoinitiator 1-hydroxycyclohexyl phenyl ketone;

(f) a cationic photoinitiator (bis[4-diphenylsulfonio)-phenyl]sulfide bis hexafluoro antimonate; and

(g) a pigment and/or a dye.

78. (New) The radiation-curable composition according to claim 77, wherein said composition further comprises one or more additives different than pigment or dye.

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The numbering of the citations which are mentioned for the first time will be adhered to in the rest of the procedure:

- (1) US 5,539,219 A
- (2) US 2004/0114059 A1
- (3) ~~US 5,691,786 A~~

The examination is based on the translation with claims 1 to 16 received on 26.08.2005.

I

It should first be noted that the dependent claims have patent-hindering deficiencies.

Subordinate claims 4 to 7 claim a storage capacitance of a thin film transistor. However, a thin film transistor per se has no storage capacitance. The claims therefore contain a contradiction.

The aforesaid comment on claims 4 to 7 applies correspondingly to claims 13 to 16.

Claim 7 also claims a relationship between a value of a storage capacitance (Farad) and a scalar ratio. However, a single transistor and single capacitor only form a single pair of values (ratio/storage capacitance) so that the relationship claimed in claim 7 between the said quantities is unclear especially as on account of the different units, the relationship can have no equality. A necessary pre-factor is undefined.

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examiner would like the submission of a supplemental oath, then applicant would be pleased to do so, but applicant believes that the original oath was proper and covers the developments in this application.

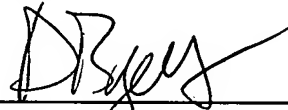
In view of the foregoing remarks, applicant submits that this application is in condition for allowance. A notice that effect is earnestly solicited.

If the examiner has any questions concerning this case, then the undersigned may be contacted at 703-816-4009.

Respectfully submitted,

**NIXON & VANDERHYE P.C.**

By: \_\_\_\_\_



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